Raman spectroscopy of ferromagnetic CrO₂

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Polarized Raman spectra of the ferromagnetic metal CrO_2 were measured in a broad temperature range including $T_c \approx 390\,$ K. The Raman-allowed modes of A_{1g} , B_{1g} , B_{2g} , and E_g symmetry were identified and compared to the corresponding modes of isostructural TiO_2 . The two low-frequency Raman lines are relatively narrow, indicating weak scattering of the corresponding B_{1g} and E_g phonons. Whereas the Raman intensities are not visibly affected by the magnetic ordering, the dependences on temperature of the phonon wave numbers exhibit peculiarities that could be attributed to a spin-phonon interaction. The variations with T of the phonon linewidths follow at low temperatures the dependence expected for phonon-phonon scattering. An additional broadening at higher temperatures with a maximum near T_c is tentatively assigned to scattering from collective spin fluctuations. [S0163-1829(99)00825-5]

Chromium dioxide, CrO₂, has attracted significant interest as it has a unique electronic band structure, resulting in halfmetallic ferromagnetism ($T_c \approx 390$ K) with completely spinpolarized electrons at E_F . ¹⁻⁴ Although there have been numerous reports on the magnetic, electric, and structural properties of CrO₂, there are few data on its phonon spectra. Symmetry analysis of the zone-center phonons of CrO₂ (space group $P4_2/mnm$) reveals that there are four Ramanactive phonon modes of A_{1g} , B_{1g} , B_{2g} , and E_g symmetry and four infrared-active phonon modes $(A_{2u} + 3E_u)$. The atomic motions corresponding to the Raman modes are shown in Fig. 1. Lewis et al.² predicted the frequency of the A_{1g} mode to be 587 cm⁻¹. Basov et al.⁷ measured the optical conductivity in the infrared frequency range and found three peaks at 357, 474, and 573 cm⁻¹, which should correspond to transverse optical phonons. No conclusion was drawn regarding the symmetry of these infrared-active vibrations.

In this work we report the polarized Raman spectra of CrO_2 as obtained from (110)- and (001)-oriented thin films on TiO_2 substrates of the same orientation. The Raman lines corresponding to the Raman-allowed phonon modes were unambiguously identified and their variation with temperature was studied between 5 and 420 K.

In the upper part of Fig. 2 are shown the Raman spectra of CrO_2 as obtained at 300 K with 632.8 nm laser excitation in four different scattering configurations, and laser excitation in $(A_{1g} + B_{2g})$, $y'(zz)\bar{y}'$ (A_{1g}) , $y'(zx')\bar{y}'$ (E_g) , and $z(x'y')\bar{z}$ (B_{1g}) scattering configurations (x', y', and z) correspond to the crystallographic directions $[1\bar{1}0]$, [110], and [001], respectively; in the brackets are the allowed phonon mode symmetries). In the lower part of Fig. 2 the corresponding spectra for the isostructural compound TiO_2 are shown. The latter spectra are identical to those reported in the pioneering work of Porto et al. Figure 3 shows the temperature evolution of the spectra of CrO_2 between 5 and 420 K. These spectra were obtained with 514.5 nm excitation from the

(110)-oriented film with incident polarization along x' and without an analyzer. Therefore they are a superposition of $y'(x'x')\bar{y}'$ ($A_{1g}+B_{2g}$) and $y'(x'z)\bar{y}'$ (E_g) spectra. In Table I are compared the wave numbers and linewidths of the Raman phonon lines of CrO_2 and TiO_2 at 300 K and 5 K as well as their relative intensities with 632.8 nm and 514.5 nm excitation. To calculate the relative intensities we fitted each phonon line by a Lorentzian and normalized its area to that of the A_{1g} line in the x'x' spectrum with the same excitation and at the same temperature.

It follows from Figs. 2 and 3 and Table I that the Raman spectra of CrO_2 and TiO_2 exhibit definite differences, namely, (i) only the one-phonon lines are pronounced in the spectra of CrO_2 in contrast to TiO_2 , where the intensity of two-phonon bands is comparable to that of the one-phonon lines; (ii) the A_{1g} and B_{2g} lines are of comparable intensity in CrO_2 , whereas in TiO_2 the B_{2g} line is weaker by two orders of magnitude; and (iii) the Raman line corresponding to the A_{1g} mode is of comparable intensity with xx(x'x') and zz scattering configurations for CrO_2 , whereas the zz

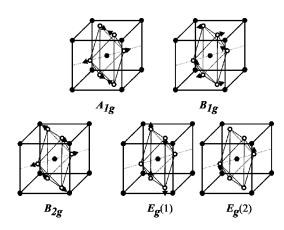


FIG. 1. Main atomic motions in the Raman modes of CrO_2 (space group $P4_2/mnm$). Only oxygen atoms participate in these modes.

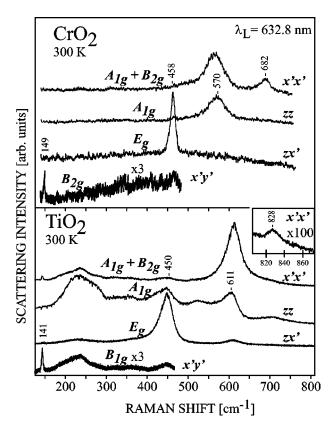


FIG. 2. Polarized Raman spectra of CrO_2 and TiO_2 as obtained at 300 K with 632.8 nm excitation.

component is much weaker in the case of TiO₂.

It is plausible to assume that the above differences in the otherwise isostructural compounds are due mainly to the different intermediate electronic states in the Raman scattering process. TiO_2 is a transparent material and the laser excitation energies (1.96 and 2.41 eV) used in our experiments are well below the gap for electronic transitions. In contrast, upon photon excitation the final states of both spin-up and spin-down electrons in CrO_2 are in the corresponding conduction bands. The Raman-scattering efficiency η for a given phonon can be expressed as 9

$$\eta = \left(\frac{\omega_s}{c}\right)^4 LV |\mathbf{e}_i \cdot \mathcal{R} \cdot \mathbf{e}_s|^2, \tag{1}$$

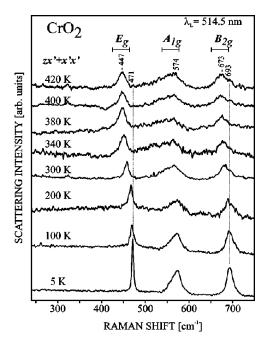


FIG. 3. Variations of the x'x' + x'z Raman spectrum of CrO_2 between 5 and 420 K. The excitation photon energy was 2.41 eV (514.5 nm).

where *i* and *s* are indices for *incident* and *scattered* radiation, *L* is the *scattering length* defined for an absorbing material as $(\alpha_i + \alpha_s)^{-1}$ (α is the absorption coefficient), *V* is the volume of the sample producing the scattered radiation (for a parallel beam with area A, V = LA), \mathbf{e}_i and \mathbf{e}_s denote the incident and scattered polarization, and \mathcal{R} is the corresponding *Raman tensor*. For the transparent range the second-rank Raman tensor \mathcal{R} is defined as

$$\mathcal{R} = \mathcal{R}^{\omega_i, \Omega} = \left(\frac{\partial \chi}{\partial \mathbf{Q}}\right)_{\mathbf{Q} = 0} \mathbf{Q}(\Omega), \tag{2}$$

where $\mathbf{Q}(\mathbf{r},t) = \mathbf{Q}(\mathbf{q},\Omega)\cos(\mathbf{q}\cdot\mathbf{r}-\Omega t)$ are the atomic displacements associated with a phonon with wave vector \mathbf{q} and frequency Ω and $\chi(\mathbf{k}_i,\omega_i,\mathbf{Q}) = \chi(\mathbf{k}_i,\omega_i) + (\partial\chi/\partial\mathbf{Q})_0\mathbf{Q}(\mathbf{r},t) + \cdots$ is the electric susceptibility. For photon energies within the range of direct interband elec-

TABLE I. Wave number and halfwidth of the Raman phonon lines of CrO_2 and TiO_2 at 300 K and 5 K, and their relative intensities with 632.3 nm and 514.5 nm laser line excitation.

Raman mode	<i>T</i> (K)	CrO_2				${ m TiO}_2$		
		Position (cm ⁻¹)	Width (cm ⁻¹)	Inter (632.8 nm)	nsity (541.5 nm)	Position (cm ⁻¹)	Width (cm ⁻¹)	Intensity (632.8 nm)
$\overline{A_{1g}}$	5	574	24		1.00(xx) 1.61(zz)	612	21	
	300	570	49	1.00(xx) 0.59(zz)	1.00(xx) 0.58(zz)	611	44	1.00(xx) 0.33(zz)
B_{1g}	5					144	3.5	
	300	149	3.0	0.01		141	3.7	0.006
B_{2g}	5	693	16		0.89			
	300	682	29	0.19	0.57	828	14.1	0.002
E_g	5	471	4.5			454	10	
	300	458	11.5	0.22		450	36	0.81

tronic transitions, in particular near a critical point, the non-zero components of \mathcal{R} may significantly increase due to a strong modulation of combined electronic densities of states [and hence of $\chi(\omega_i)$] by particular atomic vibrations. Despite the strong increase of \mathcal{R} in such resonance conditions, however, the scattering efficiency η of a light-absorbing medium as a whole decreases due to the much stronger effect of the reduced scattering length L and scattering volume V. The resonance conditions for CrO_2 do change with variation of the excitation photon energy as manifested by the significant difference of the relative intensity of the B_{2g} mode with 632.8 and 514.5 nm excitation.

The resonant conditions (and hence of the relative Raman line intensities) are expected to change also for a fixed excitation photon energy provided the electronic structure undergoes changes. For ferromagnetic materials such changes could be induced by the spin ordering, resulting in a splitting of electronic bands into spin-polarized subbands. Such a magnetic-order-dependent Raman scattering has been reported, e.g., for the ferromagnetic semiconductors CdCr₂Se₄ and CdCr₂S₄ where some of the Raman lines increase strongly upon cooling below the corresponding Curie temperatures. It has been shown that such a temperature behavior which is sensitive to the laser photon energy could be explained by the exchange splitting of the electronic bands resulting in a change of combined electronic densities of states near the energy of the laser excitation.

It follows from Fig. 3, within the accuracy of our experiments, that no redistribution of the relative intensities of the Raman lines of CrO_2 has been detected near $T_c \approx 390\,$ K. This is an indication that the combined electronic density of states near 2.4 eV is not strongly affected by magnetic ordering. Such a result indicates that Hund's rule exchange splitting is still present up to the highest temperature in our experiments (420 K) and, therefore, the electronic structure of magnetically ordered domains above T_c is very similar to the one in the ferromagnetic phase below T_c .

The variations with temperature of the position the E_g , A_{1g} , and B_{2g} Raman lines are shown in the right panels of Fig. 4. While with temperature increasing from 5 to 420 K the E_g and B_{2g} modes soften by 5.5% and 3%, respectively, the softening of the A_{1g} mode is less than 1%. As the experimental points are restricted to temperatures close to above T_c , no definite conclusion can be drawn about the effect of magnetic ordering on the phonon frequencies. Nevertheless, there are indications for anomalies near T_c in the position of both the A_{1g} and E_g modes.

The dependences of the phonon linewidth vs temperature, $\Gamma(T)$, are illustrated in the left panels of Fig. 4. At low temperatures the linewidth of the E_g phonon is relatively low (4.5 cm⁻¹). For the B_{1g} phonon, which was not measured at low temperatures, 12 an even smaller linewidth is expected as at 300 K its width is only 3 cm⁻¹, equal to the resolution of our spectrometer. The linewidth of a phonon line is a measure of the phonon scattering. The small widths of the low-frequency B_{1g} and E_g phonons, therefore, provide an evidence for a weak scattering. In contrast, the much higher linewidths of the A_{1g} and B_{2g} phonons (24 cm⁻¹ and 16 cm⁻¹, respectively, at 5 K) indicate that these phonons scatter much more strongly. This observation is consistent

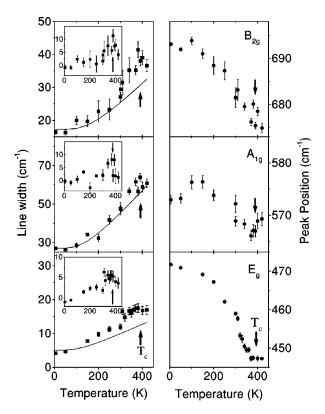


FIG. 4. Variations with temperature of the peak positions and linewidths of the E_g , A_{1g} , and B_{2g} Raman lines of CrO_2 . The solid lines in the left panels represent the corresponding functions Γ_{pp} which describe the phonon-phonon interaction. The insets show the additional broadening $\Delta\Gamma = \Gamma_{\text{exp}} - \Gamma_{pp}$ assigned to magnetic scattering.

with the results of Basov *et al.*⁷ who found that at low temperatures the electronic scattering below 500 cm⁻¹ becomes negligible.

It is plausible to assume that the dependence $\Gamma(T)$ is governed by mainly phonon-phonon scattering (anharmonic decay), described by

$$\Gamma_{pp}(T) = \Gamma_0 \left[1 + \frac{2}{\exp(\hbar\Omega/2k_B T) - 1} \right], \tag{3}$$

where Γ_0 is the linewidth at $T\!=\!0$ and Ω is the phonon frequency. The function $\Gamma_{pp}(T)$, shown by solid curve in the left panels of Fig. 4, fits satisfactorily the experimental points at low temperatures. At high temperatures, however, the experimental points lie above $\Gamma_{pp}(T)$, indicating that another channel could also be involved in the scattering process. For a magnetic material like ${\rm CrO_2}$ such an additional channel could arise from scattering from the collective spin fluctuations (spin disorder scattering) that exist near T_c . If so, the contribution of spin-disorder scattering to the phonon linewidth should pass over a maximum near T_c . The differences $\Delta \Gamma = \Gamma_{\rm exp} - \Gamma_{pp}$, shown in the insets of Fig. 4, do have a maximum near T_c , although a more definite conclusion could be drawn only after extending the measurements to higher temperatures. It is worth noting here that the local

maximum near T_c of the phonon linewidth has recently been reported for another ferromagnetic compound, SrRuO₃, which is also a "bad" metal.¹³

In conclusion, we measured the polarized Raman spectra of ferromagnetic metal CrO_2 in a broad temperature range including T_c and identified all four allowed Raman modes. The low-frequency Raman lines of B_{1g} and E_g symmetry are very narrow, indicating weak phonon scattering, in particular at low temperatures. The Raman intensities are not strongly affected by the magnetic ordering, whereas the line position

vs T dependences change their slope near T_c for the A_{1g} and E_g modes. At low temperatures the variations with T of the phonon linewidths follow the dependence expected for a phonon-phonon scattering. The additional broadening which appears with approaching T_c is tentatively assigned to the scattering of phonons from collective spin fluctuations.

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¹²In our low-temperature measurements we used an (110)- oriented film, where no scattering configurations for observation of the B_{1g} mode were available.

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